

[查询"CS65-70P"供应商](#)

CentralTM

Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

www.centrasemi.com

CS65-70B
CS65-70D
CS65-70M
CS65-70N
CS65-70P
CS65-70PB

SILICON CONTROLLED RECTIFIER
70 AMPS RMS, 200 THRU 1200 VOLTS

TO-65 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CS65-70B series types are High Power Silicon Controlled Rectifiers designed for phase control applications.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL	CS65 -70B	CS65 -70D	CS65 -70M	CS65 -70N	CS65 -70P	CS65 -70PB	UNITS
Peak Repetitive Off-State Voltage	$V_{\text{DRM}}, V_{\text{RRM}}$	200	400	600	800	1000	1200	V
Peak Non-Repetitive Reverse Voltage	V_{RSM}	300	500	700	900	1100	1300	V
RMS On-State Current ($T_C=102^{\circ}\text{C}$)	$I_{\text{T(RMS)}}$				63			A
Average On-State Current ($T_C=102^{\circ}\text{C}$)	$I_{\text{T(AV)}}$				40			A
Peak One Cycle Surge (60Hz)	I_{TSM}				1000			A
I^2t Value for Fusing ($t=8.3\text{ms}$)	I^2t				4100			A^2s
Peak Forward Gate Voltage	V_{FGM}				20			V
Peak Reverse Gate Voltage	V_{RGM}				10			V
Peak Gate Power	P_{GM}				10			W
Average Gate Power ($t_p=10\mu\text{s}$)	$P_{\text{G(AV)}}$				1.0			W
Peak Gate Current	I_{GM}				3.0			A
Critical Rate of Rise of On-State Current	di/dt				200			$\text{A}/\mu\text{s}$
Storage Temperature	T_{stg}				-65 to +150			$^{\circ}\text{C}$
Junction Temperature	T_{J}				-65 to +125			$^{\circ}\text{C}$
Thermal Resistance	$\Theta_{\text{J-C}}$				0.35			$^{\circ}\text{C}/\text{W}$

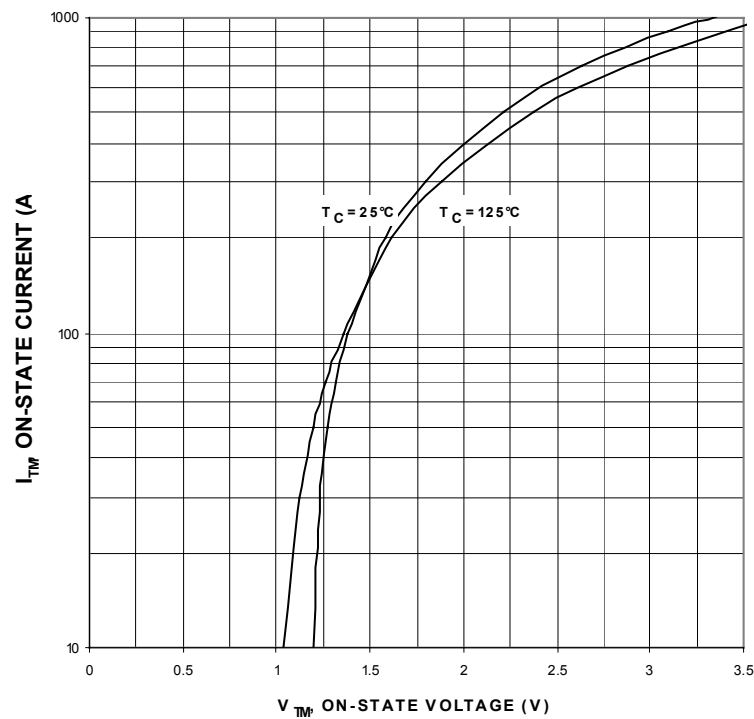
ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{\text{DRM}}, I_{\text{RRM}}$	Rated $V_{\text{DRM}}, V_{\text{RRM}}, T_C=125^{\circ}\text{C}$			6.0	mA
I_{GT}	$V_{\text{D}}=12\text{V}, R_{\text{L}}=33\Omega$			100	mA
I_{H}	$I_{\text{T}}=500\text{mA}$			200	mA
V_{GT}	$V_{\text{D}}=12\text{V}, R_{\text{L}}=33\Omega$			3.0	V
V_{TM}	$I_{\text{TM}}=500\text{A}$			3.0	V
dv/dt	$V_{\text{D}}=.67 \times V_{\text{DRM}}, T_C=125^{\circ}\text{C}$	200			$\text{V}/\mu\text{s}$

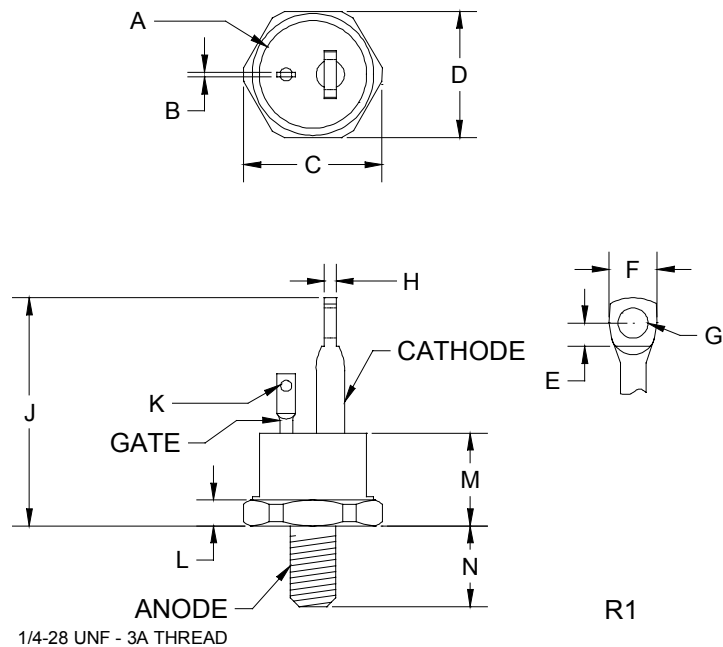
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[查询“CS65-70B”供应商](#)

MAXIMUM ON-STATE CHARACTERISTICS



TO-65 PACKAGE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	-	0.667	-	16.94
B	0.025	0.030	0.64	0.76
C	-	0.770	-	19.56
D	0.677	0.685	17.20	17.40
E	0.120	-	3.05	-
F	0.200	0.300	5.08	7.62
G (DIA)	0.145	0.155	3.68	3.93
H	0.065	0.085	1.65	2.15
J	1.200	1.250	30.48	31.75
K (DIA)	0.055	0.065	1.40	1.65
L	0.115	0.155	2.92	3.94
M	-	0.515	-	13.08
N	0.427	0.447	10.84	11.35
TO-65 (REV: R1)				